2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLF888E (S			ompinioa oatimo	Grupino Gymbol
-				
1	drain1 (peak)		1 2	4
2	drain2 (main)			ل
3	gate1 (peak)		5	<u> </u>
4	gate2 (main)		3 4	5
5	source	<u>[1]</u>		4 7
				'⊢¬
				2 sym117
				3,
BLF888ES (SOT539B)			
1	drain1 (peak)			
2	drain2 (main)		1 2	1
3	gate1 (peak)		5	ļ ļ
4	gate2 (main)		3 4	3 — 5
5	source	<u>[1]</u>		4 7
				li⊢_
				2
				sym117

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage				
	Name	Description	Version			
BLF888E	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A			
BLF888ES	-	earless flanged balanced ceramic package; 4 leads	SOT539B			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{DS}(amp)main}$	main amplifier drain-source voltage		-	104	٧
$V_{DS(amp)peak}$	peak amplifier drain-source voltage		-	120	٧
$V_{GS(amp)main}$	main amplifier gate-source voltage		-0.5	+11	٧
$V_{GS(amp)peak}$	peak amplifier gate-source voltage		-6	+11	٧
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 90 ^{\circ}\text{C}; V_{DS} = 50 \text{V};$ $I_{DS} = 3 \text{A (main)}; I_{DS} = 0 \text{A (peak)}$	0.29	K/W
		T _{case} = 90 °C; V _{DS} = 50 V; P _L = 150 W; PAR = 8 dB	0.19	K/W

^[1] Measured under DC test conditions, with peak section off.

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.4 \text{ mA}$	104	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 240 mA	1.25	1.75	2.25	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	38	-	A
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V	-	-	280	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 8.5 \text{ A}$	-	120	-	mΩ
Peak dev	rice					_
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3.6 \text{ mA}$	125	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 360 mA	1.33	1.83	2.33	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	57	-	Α
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V	-	-	280	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 12.6 \text{ A}$	-	90	-	mΩ

Table 7. AC characteristics

 T_i = 25 °C; per section unless otherwise specified.

,	' I	•				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	vice		•			
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 50 V; f = 1 MHz	-	210	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	67	-	pF
C _{rss}	reverse transfer capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	1.35	-	pF

BLF888E_BLF888ES

^[2] Measured in an ultra-wide Doherty application, using DVB-T (8k OFDM) signal, PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

 Table 7.
 AC characteristics ...continued

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Peak de	vice					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	315	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	105	-	pF
C _{rss}	reverse transfer capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	1.5	-	pF

Table 8. RF characteristics

RF characteristics in Ampleon production test circuit, T_{case} = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
DVB-T (8	DVB-T (8k OFDM), Doherty operation						
V _{DS}	drain-source voltage		-	50	-	V	
I_{Dq}	quiescent drain current	peak section: $V_{GS} = 1.3 \text{ V}$ below $V_{GS(th)}$ (peak)	-	600	-	mA	
$P_{L(AV)}$	average output power	f = 550 MHz	-	150	-	W	
G _p	power gain	f = 550 MHz	15.8	17	-	dB	
η_{D}	drain efficiency	f = 550 MHz	48	52	-	%	
PAR	peak-to-average ratio	f = 550 MHz	7.2	7.8	-	dB	

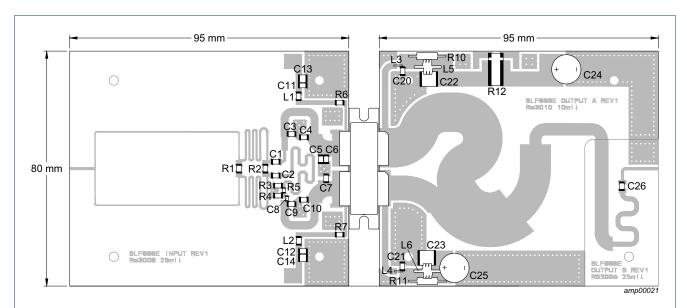
7. Test information

7.1 Ruggedness in Doherty operation

The BLF888E and BLF888ES are capable of withstanding a load mismatch corresponding to VSWR \geq 40 : 1 through all phases under the following conditions: V_{DS} = 50 V; f = 550 MHz at rated load power.

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7.2 Test circuit



Printed-Circuit Board (PCB): Rogers 3006; ϵ_r = 6.5 F/m; height = 0.635 mm; Cu (top/bottom metalization); thickness copper plating = 29.6 μ m; Rogers 3010: ϵ_r = 10 F/m; height = 0.254 mm

See Table 9 for a list of components.

Fig 1. Component layout for production RF test circuit

Table 9. List of components For test circuit see Figure 1.

Component	Description	Value	Remarks
C1, C2	multilayer ceramic chip capacitor	51 pF [1]	ATC 100B
C3	multilayer ceramic chip capacitor	11 pF [1]	ATC 100B
C4	multilayer ceramic chip capacitor	13 pF [1]	ATC 100B
C5, C6	multilayer ceramic chip capacitor	24 pF [1]	ATC 100B
C7	multilayer ceramic chip capacitor	33 pF [1]	ATC 100B
C8	multilayer ceramic chip capacitor	51 pF [2]	ATC 100A
C9	multilayer ceramic chip capacitor	12 pF [1]	ATC 100B
C10	multilayer ceramic chip capacitor	20 pF [1]	ATC 100B
C11, C12	multilayer ceramic chip capacitor	43 pF [1]	ATC 100B
C13, C14	multilayer ceramic chip capacitor	4.7 μF	
C20, C21	electrolytic capacitor	100 pF [1]	ATC 100B
C22, C23	multilayer ceramic chip capacitor	4.7 μF, 100 V	
C25, C25	electrolytic capacitor	470 μF, 63 V	
C26	multilayer ceramic chip capacitor	47 pF [1]	ATC 100B
L1, L2	inductor	10 nH	Coilcraft
L3, L4	inductor	0.5 turn, D = 2 mm, d = 1mm	
L5, L6	inductor	1 turn, D = 5 mm, d = 1mm	
R1	chip resistor	90 Ω	

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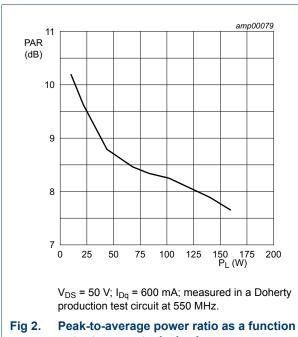
List of components ...continued Table 9. For test circuit see Figure 1.

Component	Description	Value	Remarks
R2	chip resistor	265 Ω	
R3, R4	chip resistor	360 Ω	
R5	chip resistor	15 Ω	
R6	chip resistor	75 Ω	
R7	chip resistor	5 Ω	
R10, R11	wire resistor	1 Ω	
R12	shunt resistor	0.01 Ω	

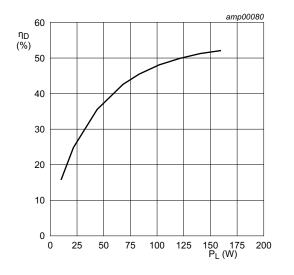
- [1] American Technical Ceramics type 100B or capacitor of same quality
- [2] American Technical Ceramics type 100A or capacitor of same quality

7.3 Graphical data

7.3.1 DVB-T in production test circuit



Peak-to-average power ratio as a function of output power; typical values



 V_{DS} = 50 V; I_{Dq} = 600 mA; measured in a Doherty production test circuit at 550 MHz.

Fig 3. Drain efficiency as a function of output power; typical values

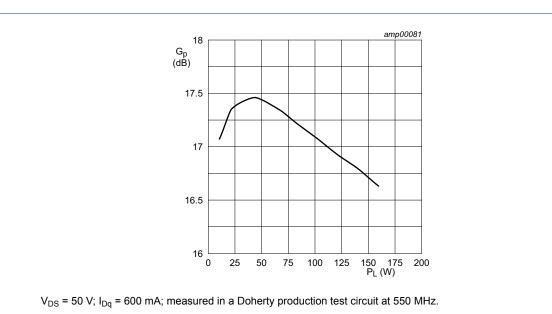


Fig 4. Power gain as a function of output power; typical values

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8. Package outline

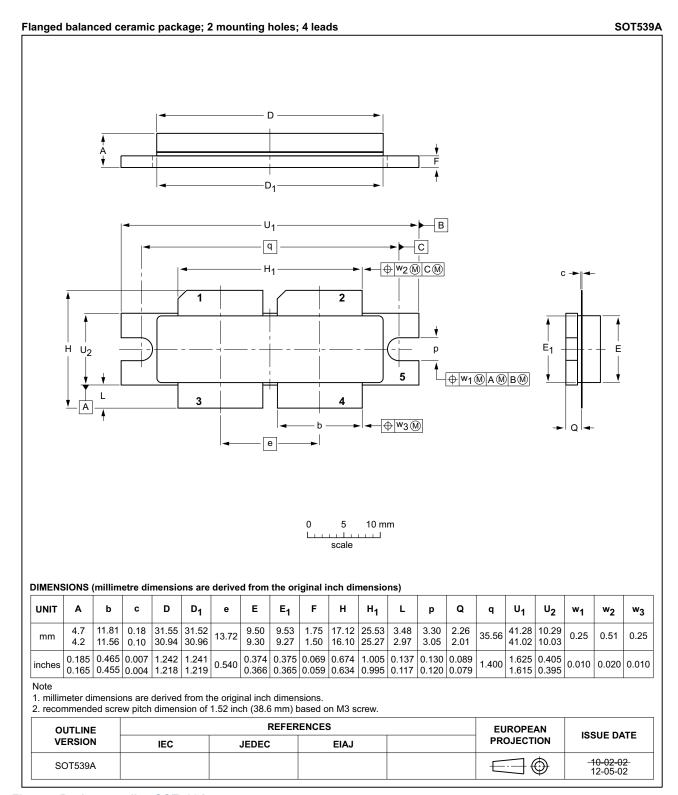


Fig 5. Package outline SOT539A

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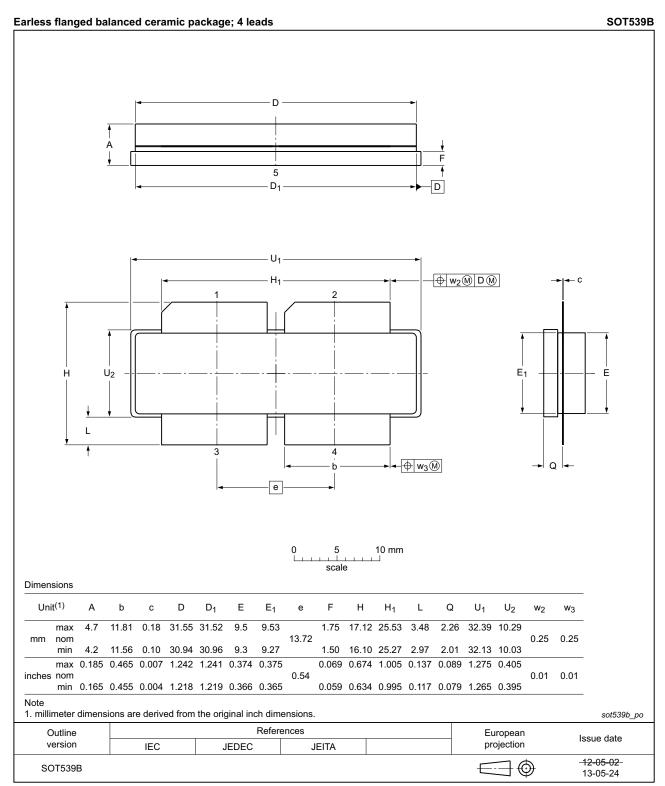


Fig 6. Package outline SOT539B

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9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description	
CCDF	Complementary Cumulative Distribution Function	
DVB-T	Digital Video Broadcast - Terrestrial	
ESD	ElectroStatic Discharge	
LDMOS	Laterally Diffused Metal-Oxide Semiconductor	
MTF	Median Time to Failure	
OFDM	Orthogonal Frequency Division Multiplexing	
PAR	Peak-to-Average Ratio	
UHF	Ultra High Frequency	
VSWR	Voltage Standing Wave Ratio	

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF888E_BLF888ES v.2	20160830	Product data sheet	-	BLF888E_BLF888ES v.1	
Modifications:	Section 1.1	on page 1: section update	ed		
	Table 1 on p	age 1: table updated			
	Section 1.2	on page 1: text second lis	t item updated		
	Table 5 on p	age 3: table updated			
	Table 6 on p	age 3: table updated			
	Table 8 on p	age 4: table updated			
	Section 7.1 on page 4: section updated				
	Section 7.3 on page 6: section added				
BLF888E_BLF888ES v.1	20160317	Objective data sheet	-	-	

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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UHF power LDMOS transistor

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UHF power LDMOS transistor

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Date of release: 30 August 2016 Document identifier: BLF888E_BLF888ES